

### 5 A Schottky Barrier Rectifier

### DESCRIPTION

This UPS540e3 in the Powermite3<sup>®</sup> package is a high efficiency Schottky rectifier that is also RoHS compliant offering high current/power capabilities previously found only in much larger packages. They are ideal for SMD applications that operate at high frequencies. In addition to its size advantages, the Powermite3<sup>®</sup> package includes a full metallic bottom that eliminates the possibility of solder flux entrapment during assembly and a unique locking tab act as an efficient heat path to the heat-sink mounting. Its innovative design makes this device ideal for use with automatic insertion equipment.

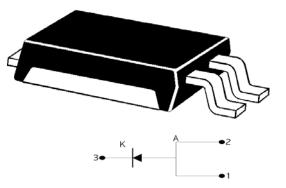
IMPORTANT: For the most current data, consult MICROSEMI's website: http://www.microsemi.com

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ABSOLUTE MAXIMUM RATINGS AT 25° C (UNLESS OTHERWISE SPECIFIED)					
Symbol	Value	Unit			
V <sub>RRM</sub> V <sub>RWM</sub> V <sub>R</sub>	40	v			
V <sub>R (RMS)</sub>	28	V			
Ι <sub>ο</sub>	5	А			
I <sub>FSM</sub>	100	A			
T <sub>STG</sub>	-55 to +150	°C			
$T_J$	-55 to +125	°C			
	/ISE SPEC Symbol V <sub>RRM</sub> V <sub>RWM</sub> V <sub>R</sub> V <sub>R</sub> (RMS) I <sub>0</sub> I <sub>FSM</sub> T <sub>STG</sub>	SymbolValue $V_{RRM}$ $V_{RWM}$ $V_R$ 40 $V_{R(RMS)}$ 28 $I_0$ 5 $I_{FSM}$ 100 $T_{STG}$ -55 to +150	/ISE SPECIFIED)SymbolValueUnit $V_{RRM}$ $V_{RWM}$ 40V $V_{RWM}$ $V_R$ 28V $V_R$ (RMS)28V $I_0$ 5A $I_{FSM}$ 100A $T_{STG}$ -55 to +150°C		

#### THERMAL CHARACTERISTICS

Thermal Resistance			
Junction-to-case (bottom)	R <sub>θJC</sub>	3.2	°C/ Watt
Junction to ambient (1)	$R_{\theta JA}$	65	°C/ Watt
(1) When mounted on FR-4 PC board using 2 oz copper with recommended minimum foot print			

#### Powermite 3<sup>™</sup>



#### **KEY FEATURES**

- Very low thermal resistance package
- RoHS Compliant with e3 suffix part number
- Guard-ring-die construction for transient protection
- Efficient heat path with Integral locking bottom metal tab
- Low forward voltage
- Full metallic bottom eliminates flux entrapment
- Compatible with automatic insertion
  - Low profile-maximum height of 1mm
- Options for screening in accordance with MIL-PRF-19500 for JAN, JANTX, and JANTXV are available by adding MQ, MX, or MV prefixes respectively to part numbers. For example, designate MXUPS540e3 for a JANTX (consult factory for Tin-Lead plating).
- Optional 100% avionics screening available by adding MA prefix for 100% temperature cycle, thermal impedance and 24 hours HTRB (consult factory for Tin-Lead plating)

#### APPLICATIONS/BENEFITS

- Switching and Regulating Power Supplies.
- Silicon Schottky (hot carrier) rectifier for minimal reverse voltage recovery
- Elimination of reverse-recovery oscillations to reduce need for EMI filtering
- Charge Pump Circuits
- Reduces reverse recovery loss with low I<sub>RM</sub>
- Small foot print 190 X 270 mils (1:1 Actual size) See mounting pad details on pg 3

#### **MECHANICAL & PACKAGING**

- CASE: Void-free transfer molded thermosetting epoxy compound meeting UL94V-0
- FINISH: Annealed matte-Tin plating over copper and readily solderable per MIL-STD-750 method 2026 (consult factory for Tin-Lead plating)
- POLARITY: See figure (left)
- MARKING: S540
- WEIGHT: 0.072 gram (approx.)
- Package dimension on last page
- Tape & Reel option: 16 mm tape per Standard EIA-481-B, 5000 on 13" reel

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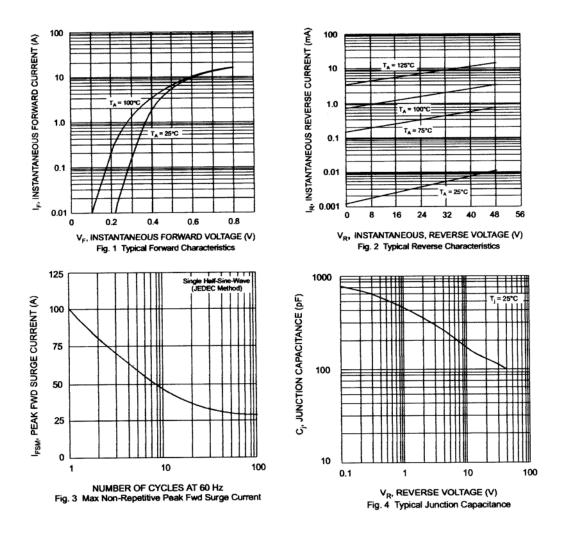
UPS340E3



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ELECTRICAL PARAMETERS @ 25°C (unless otherwise specified)						
Parameter	Symbol	Conditions	Min	Тур.	Max	Units
Forward Voltage (Note 1)				0.47	0.54	
Torward Voltage (Note T)	V <sub>F</sub>	$ I_F = 5 A, T_j = 25 °C  I_F = 5 A, T_j = 125 °C  I_F = 10 A, T_j = 25 °C  I_F = 10 A, T_j = 125 °C  I_F = 10 A, T_j = 125 °C $		0.47 0.45 0.62 0.59	0.54	V
Reverse Break Down Voltage (Note 1)	V <sub>BR</sub>	I <sub>R</sub> = 0.5 mA	40			V
Reverse Current (Note1)	I <sub>F</sub>	V <sub>R</sub> = 40 V, T <sub>j</sub> = 25°C V <sub>R</sub> = 40 V, T <sub>j</sub> =125 °C		0.030 2.5	0.5 20	mA
Capacitance	C <sub>T</sub>	V <sub>R</sub> = 4 V; F = 1 MH <sub>Z</sub>		250		pF

Note: 1 Short duration test pulse used to minimize self - heating effect

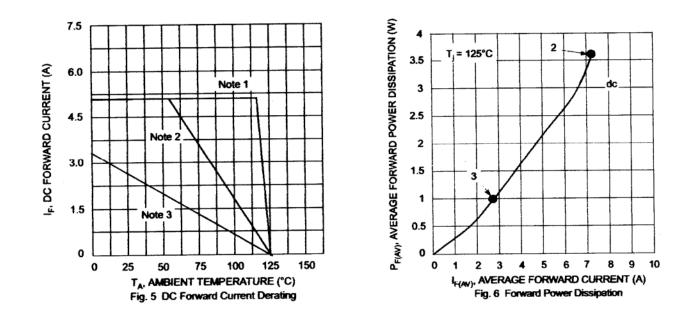


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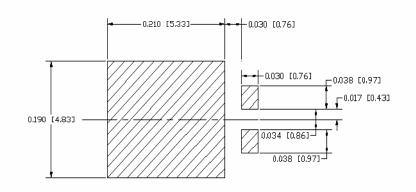
UPS340E3



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- Notes: 1. T<sub>A</sub> = T<sub>SOLDERING POINT</sub>, R<sub>ΘJS</sub>=3.2°C/W, R<sub>Θsa</sub> = 0° C/W.
  2. Device mounted on GETEK substrate, 2" x 2", 2 oz. copper, double-sided, cathode pad dimensions 0.75" x 1.0", anode pad dimensions 0.25" x 1.0". R<sub>ΘJA</sub> in range of 15-30° C/W.
  - 3. Device mounted on FRA-4 substrate, 2" x 2", 2 oz. copper, single-sided, pad layout  $R_{\Theta JA}$  in range of 65° C/W. See mounting pad below.



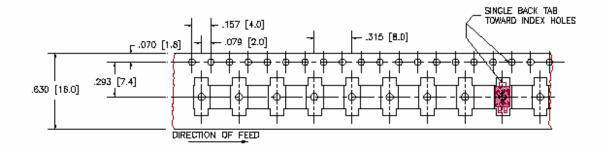
Mounting Pad Dimensions: inches [mm]

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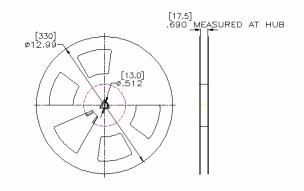


## 5 A Schottky Barrier Rectifier

16 mm TAPE



13 INCH REEL



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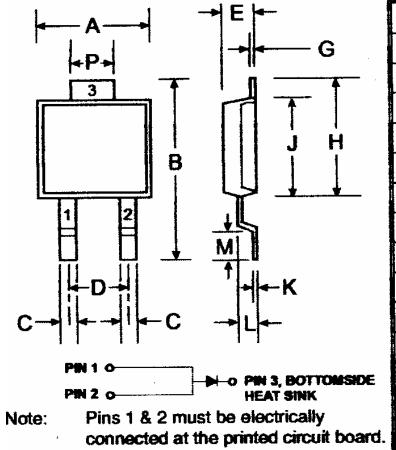
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#### DIMENSIONS



POWERMITE®3			
Dim	Min Max		
A	4.03	4.09	
B	6.40	6.61	
С	.889 NOM		
D	1.83 NOM		
E	1.10	1.14	
G	.178 NOM		
н	5.01	5.17	
J	4.37	4.43	
K	.178 NOM		
L	.71	.77	
N	.36	.46	
P	1.73	1.83	
All Dimensions in mm			



# UPS540e3

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UPS340E3 NOTES